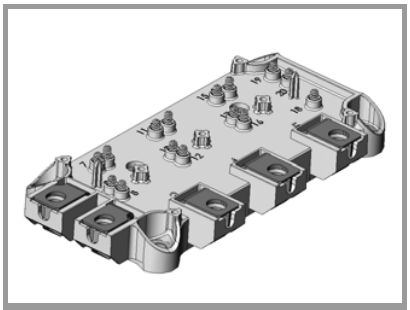
SEMiX241DH16s



SEMiX® 13

Bridge Rectifier Module (halfcontrolled)

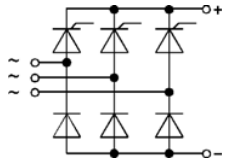
SEMiX241DH16s

Features

- Terminal height 17 mm
- Chips soldered directly to isolated substrate

Typical Applications*

- Input Bridge Rectifier for AC/DC motor control
- Power supply



DH

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Chip				
$I_{T(AV)}$	sinus 180°	T_c = 85 °C	240	A
		T_c = 100 °C	200	A
I_{TSM}	10 ms	T_j = 25 °C	2250	A
		T_j = 130 °C	1900	A
i^2t	10 ms	T_j = 25 °C	25300	A^2s
		T_j = 130 °C	18000	A^2s
V_{RSM}			1700	V
V_{RRM}			1600	V
V_{DRM}			1600	V
$(di/dt)_{cr}$	T_j = 130 °C		100	A/µs
$(dv/dt)_{cr}$	T_j = 130 °C		1000	V/µs
T_j			-40 ... 130	°C
Module				
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50Hz	1 min	4000	V
		1 s	4800	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Chip						
V_T	T_j = 25 °C, I_T = 300 A				1.9	V
$V_{T(TO)}$	T_j = 130 °C				0.85	V
r_T	T_j = 130 °C				4	mΩ
I_{DD};I_{RD}	T_j = 130 °C, V_{DD} = V_{DRM}; V_{RD} = V_{RRM}				24	mA
t_{gd}	T_j = 25 °C, I_G = 1 A, di_G/dt = 1 A/µs			1		µs
t_{gr}	V_D = 0.67 * V_{DRM}			2		µs
t_q	T_j = 130 °C			150		µs
I_H	T_j = 25 °C			150	250	mA
I_L	T_j = 25 °C, R_G = 33 Ω			300	600	mA
V_{GT}	T_j = 25 °C, d.c.		3			V
I_{GT}	T_j = 25 °C, d.c.		150			mA
V_{GD}	T_j = 130 °C, d.c.				0.25	V
I_{GD}	T_j = 130 °C, d.c.				6	mA
$R_{th(j-c)}$		per thyristor				K/W
		per module				K/W
$R_{th(j-c)}$	sin. 180°	per thyristor			0.32	K/W
		per module			0.32	K/W
$R_{th(j-c)}$		per thyristor				K/W
		per module				K/W
Module						
$R_{th(c-s)}$	per chip					K/W
	per module			0.04		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t	to terminals (M6)		2.5		5	Nm
a					5 * 9,81	m/s^2
w				350		g

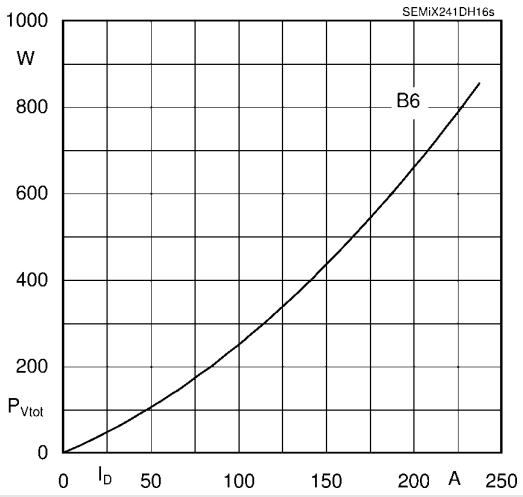


Fig. 4L: Power dissipation per module vs. direct current

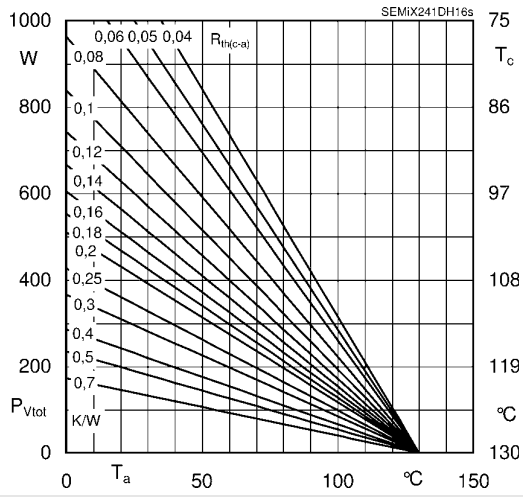


Fig. 4R: Power dissipation per module vs. case temperature

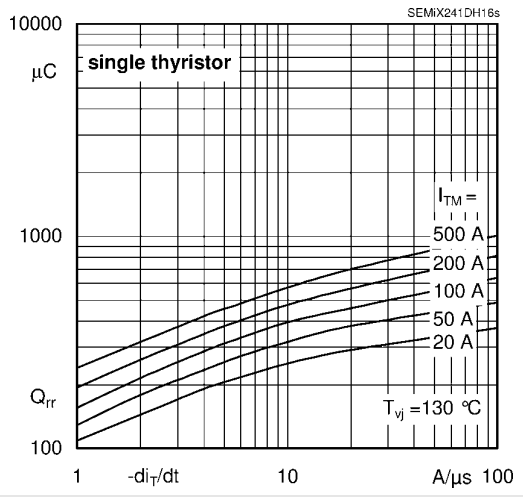


Fig. 5: Recovered charge vs. current decrease

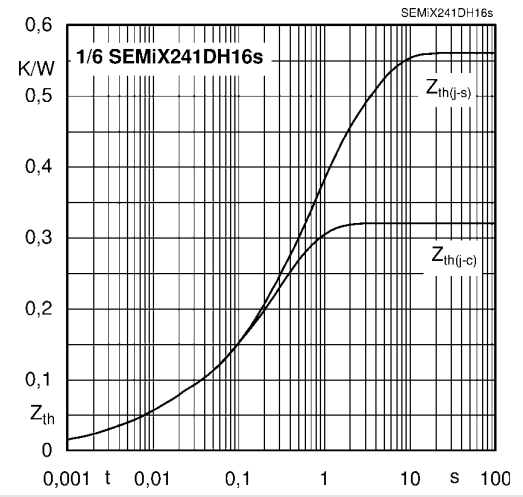


Fig. 6: Transient thermal impedance vs. time

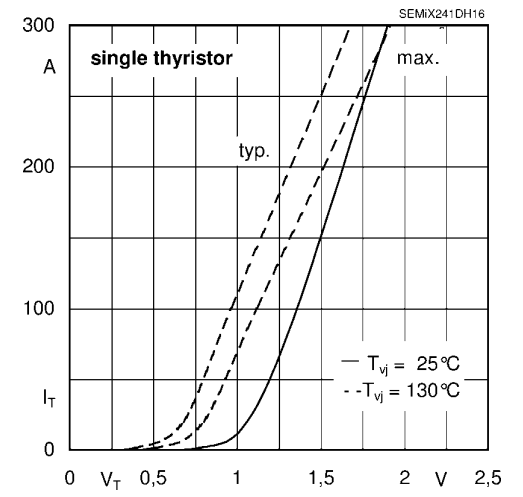


Fig. 7: On-state characteristics

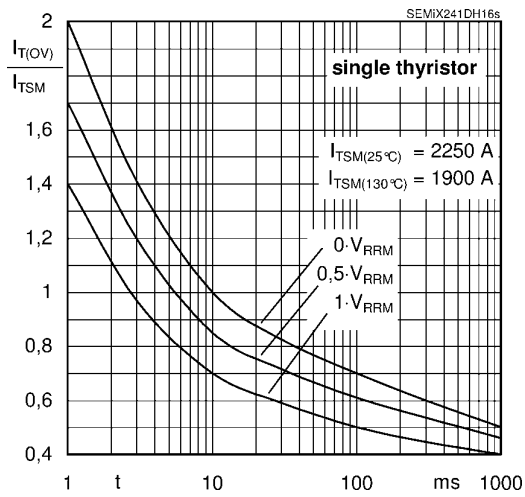


Fig. 8: Surge overload current vs. time

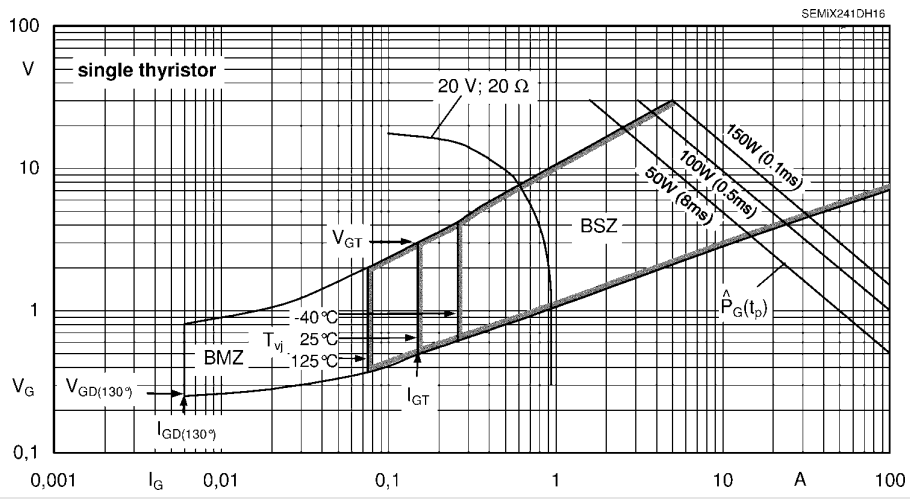
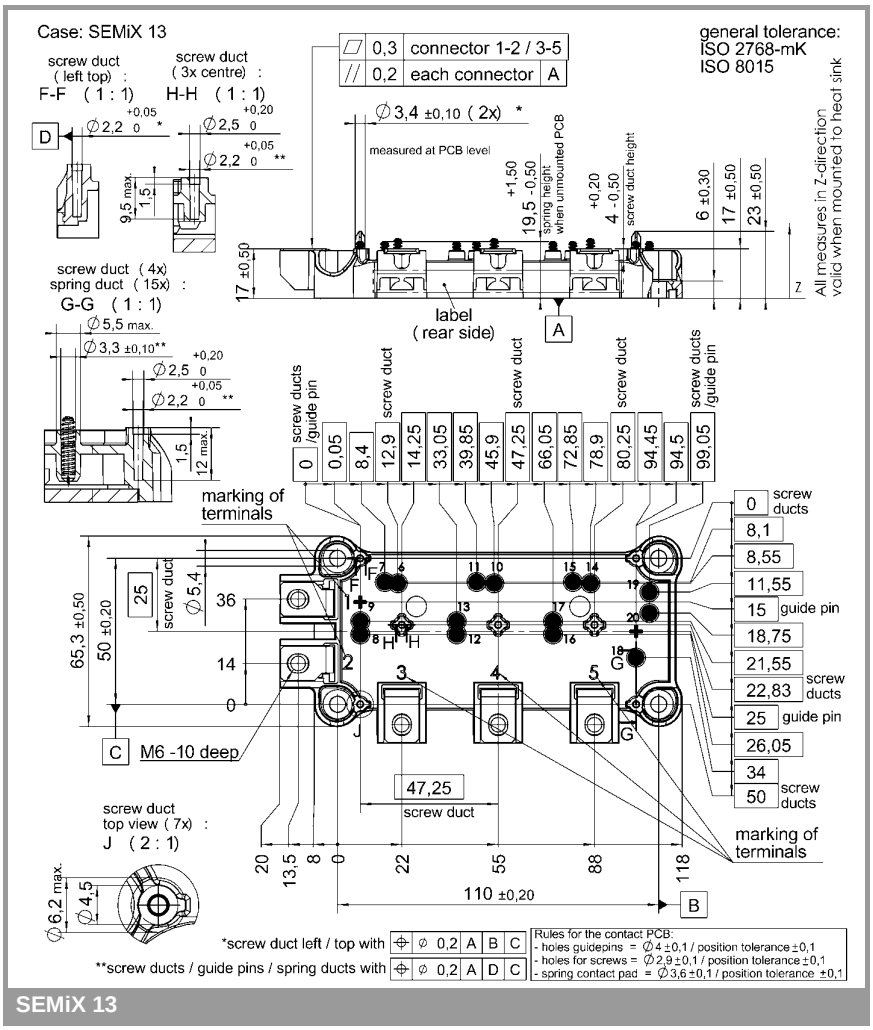
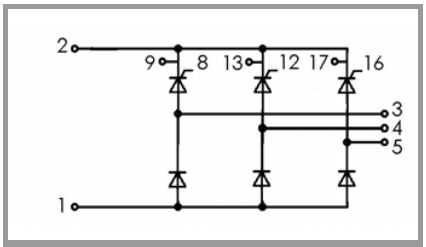


Fig. 9: Gate trigger characteristics



SEMiX 13



spring configuration

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.